

SUPPORTING INFORMATION

Table S1. Annealing temperatures and times for samples 1-10

Sample Nr	Annealing temperature, °C	Annealing time at given temperature, min
1	200	30
2	300	30
3	400	30
4	500	30
5	600	30
6	400	5
7	400	10
8	400	30
9	400	60
10	400	180

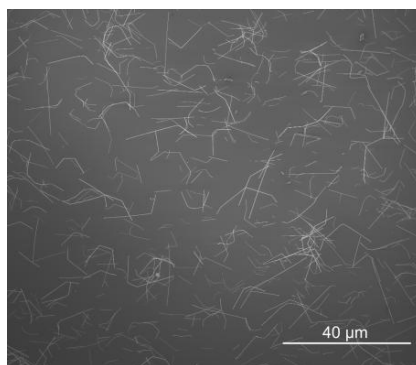


Figure S1. Typical SEM image of AgNW Network on silicon substrate

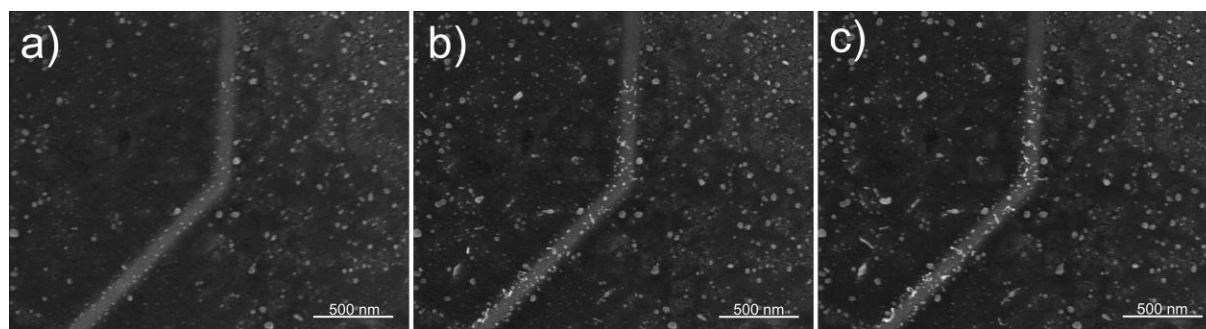


Figure S2. Time series SEM images showing Ag fibres growth on TiO₂ surface: a) beginning b) after 30 second and c) after 1 minute.

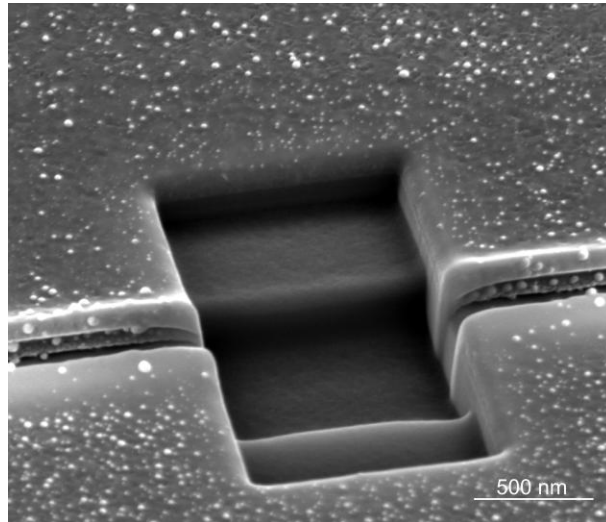


Figure S3. Typical cross-section of the TiO_2 layer after annealing at 400°C . No whiskers can be seen due to destructive effect of ion beam while taking the image in ion beam mode.